rfmd.com

RF1201

BROADBAND 10W SPDT SWITCH

Package: QFN, 6-Pin, 2mm x 2mm x 0.85mm

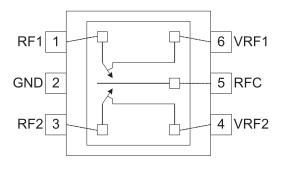


Features

- Low Frequency 2.5 GHz Operation
- Low Insertion Loss: 0.3dB at 1GHz
- High Isolation: 26dB at 1GHz
- Low Control Voltage: 2.6V to 5.0V
- Operation at 1.8V Control for Low Power Applications
- Excellent Harmonic
 Performance: -80dBc at
 1GHz
- High P0.1dB: 40dBm
- GaAs pHEMT Process

Applications

- Cellular Handset Applications
- Antenna Tuning Applications
- Multi-Mode GSM, WCDMA Applications
- IEEE802.11b/g WLAN Applications
- GSM/GPRS/EDGE Switch Applications
- Cellular Infrastructure Applications



Functional Block Diagram

Product Description

The RF1201 is a single-pole double-throw (SPDT) switch designed for switching applications which require very high power handling capability along with exceptional linearity. The RF1201 is ideally suited for battery operated applications requiring high performance switching with very low DC power consumption. The part builds upon RFMD's 0.5 umGaAs pHEMT process, and is packaged in a very compact 2mmx2mmx0.85mm, 6-Pin, leadless QFN package.

Ordering Information

RF1201 Broadband 10W SPDT Switch
RF1201PCBA-410 Fully Assembled Evaluation Board

Optimum Technology Matching® Applied

☐ GaAs HBT	☐ SiGe BiCMOS	▼ GaAs pHEMT	☐ GaN HEM
GaAs MESFET	☐ Si BiCMOS	☐ Si CMOS	☐ BiFET HBT
☐ InGaP HBT	☐ SiGe HBT	☐ Si BJT	☐ LDMOS

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RF1201



Absolute Maximum Ratings

Parameter	Rating	Unit
V _{RF1} , V _{RF2}	7.0	V
Maximum Input Power		
0.88GHz (25°C, 50Ω)	+42	dBm
1.88GHz (25°C, 50Ω)	+41	dBm
Operating Temperature	-30 to +85	°C
Storage Temperature	-35 to +100	°C



Caution! ESD sensitive device.

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implied.

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RFMD Green: RoHS compliant per EU Directive 2002/95/EC, halogen free per IEC 61249-2-21, < 1000 ppm each of antimony trioxide in polymeric materials and red phosphorus as a flame retardant, and <2% antimony in solder.

Parameter		Specification		Unit	Condition	
Farameter	Min.	Тур.	Max.	Unit	Condition	
					Temp=25°C, V _{CONTROL} =2.65V	
Insertion Loss						
RF1-ANT, RF2-ANT		0.3	0.4	dB	RF ON, 0.88GHz	
RF1-ANT, RF2-ANT		0.4	0.5	dB	RF ON, 1.88 GHz	
RF1-ANT, RF2-ANT		0.5	0.6	dB	RF ON, 2.10 GHz	
RF1-ANT, RF2-ANT		0.55	0.65	dB	RF ON, 2.45 GHz	
RF>ANT Isolation						
RF1-ANT, RF2-ANT	25	26		dB	RF ON, 0.88GHz	
RF1-ANT, RF2-ANT	21	22		dB	RF ON, 1.88GHz	
RF1-ANT, RF2-ANT	19	20		dB	RF ON, 2.10GHz	
RF1-ANT, RF2-ANT	17	18		dB	RF ON, 2.45 GHz	
0.8GHz to 1GHz Harmonics						
Second Harmonic		-80		dBc	P _{IN} =34.5dBm, 0.88GHz, 2f ₀	
Third Harmonic		-75		dBc	P _{IN} =34.5dBm, 0.88GHz, 3f ₀	
1.7 GHz to 2.0 GHz Harmonics						
Second Harmonic		-80		dBc	P _{IN} =31.5dBm, 1.9GHz, 2f ₀	
Third Harmonic		-80		dBc	P _{IN} =31.5dBm, 1.9GHz, 3f ₀	
2.45 GHz Harmonics						
Second Harmonic		-90		dBc	P _{IN} =31.5dBm, 1.9GHz, 2f ₀	
Third Harmonic		-90		dBc	P _{IN} =31.5dBm, 1.9GHz, 3f ₀	
IIP2						
RF1-ANT, RF2-ANT (Cell)		114		dBm	Tone 1: 824MHz @ 26dBm, Tone 2: 1693MHz @ -20dBm, Receive Freq: 869MHz	
RF1-ANT, RF2-ANT (AWS)		115		dBm	Tone 1: 1710 MHz @ 26dBm, Tone 2: 3820 MHz @ -20dBm, Receive Freq: 2110 MHz	
RF1-ANT, RF2-ANT (PCS)		117		dBm	Tone 1: 1850MHz @ 26dBm, Tone 2: 3780MHz @ -20dBm, Receive Freq: 1930MHz	
Triple Beat Ratio (TBR)						
RF1-ANT, RF2-ANT (Cell)		88		dBc	VSWR=2:1, Temp=15°C, 25°C, 60°C; Jammer Freq=881.5 MHz	
RF1-ANT, RF2-ANT (PCS)		88		dBc	VSWR=2:1, Temp=15°C, 25°C, 60°C; Jammer Freq=1960 MHz	



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Parameter	Min.	Тур.	Max.	Unit	Condition
RF Port Return Loss					
RF>ANT		15		dB	0.5 GHz to 2.5 GHz
Input Power at 0.1dB Compression Point					
		41		dBm	0.88GHz
		40		dBm	1.88GHz
Switching Speed					
			5	μs	
Supply and Control Signal Characteristics					
Control Voltage					
V_{HIGH}		2.65	5.00	V	
V_{LOW}			0.2	V	
Control Current			20	μΑ	

Note: Parameters hold at 25 °C and V_{CONTROL} = 2.65 V.

Switch Control Settings

,	Control Signals		Signal Paths		
,	VRF1	VRF2	RF1-RFC	RF2-RFC	
Valid States	1	0	ON	OFF	
	0	1	OFF	ON	
Invalid	0	0	Indetermin	ate State*	
States	1	1	Indetermin	ate State*	

0: Logic level low, 0V~0.2V

1: Logic level high, 2.6V~5.0V

Note: In indeterminate states, both signal paths are ON with degraded performance.



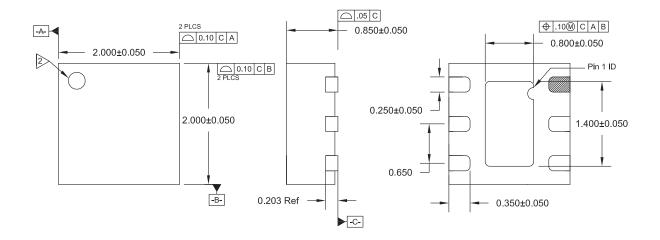
Pin	Function	Description	Interface Schematic
1	RF1	First RF connection.	
2	GND	Ground.	
3	RF2	Second RF connection.	
4	VRF2	Second RF control.	
5	RFC	Common RF connection.	
6	VRF1	First RF control.	
Pkg	GND		
Base			

Package Drawing QFN, 6-pin, 2x2

NOTES:

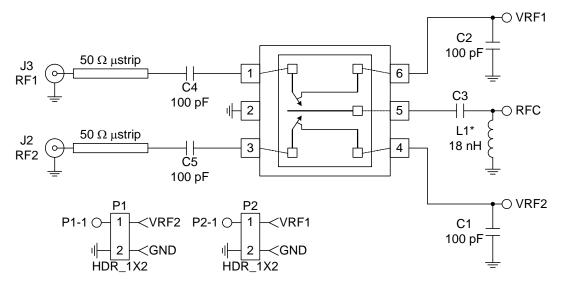
1. SHADED PIN IS LEAD 1.

2. PIN 1 IDENTIFIER MUST EXIST ON TOP SURFACE OF PACKAGE BY IDENTIFICATION MARK OR FEATURE ON THE PACKAGE BODY. EXACT SHAPE AND SIZE IS OPTIONAL.



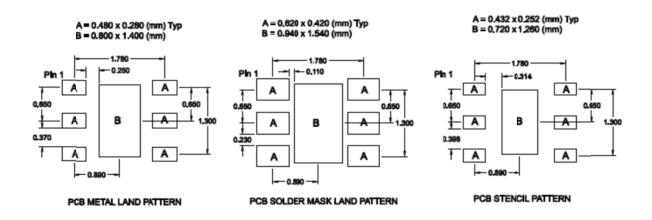


Evaluation Board Schematic



*L1 is optional for IEC61000-4-2 ESD protection.

PCB Design Requirements





Typical Performance

Temp=25°C, V_{CONTROL}=2.65V

